| | er: | 202 | 01109000.1 | | | PCN Date: Nov 10, 2020 | | | 0, 2020 |
|---|---|-----------------------------------|--|---|---|---|--|--|--|
| Title: Qualification of RFAB as an additional Fab site option using qualifie | | | | | ed Proc | | | | |
| Technology, Die Revision and New Assembly Material for select devices | | | | | | | | | |
| Customer Contact: | | | PCN Manager | | | ept: | | Quality Services | |
| Proposed 1 st Ship Date: | | | Feb 10, 2021 | | Estimate Availabil | | npie | Date provided at sample request. | |
| Change Ty | - | | | | | | | | |
| Assembly Site | | | | ssembly Proce | | | Assembly Materials | | |
| Design | | | Electrical Specification | | | | Mechanical Specification | | |
| Test Site | | | Packing/Shipping/Labeling | | | | | est Process | |
| Wafer Bump Site Wafer Fab Site | | | Wafer Bump MaterialXWafer Fab Materials | | | | Wafer Bump Process X Wafer Fab Process | | |
| ⊠ Wafer | rad Sile | | | | | | | | |
| | | | | art number ch | | | | | |
| Descriptio | | | | PCN De | lans | | | | |
| additional W | Vafer Fab s fected" sec site: | source ar tion. Dev | nd new / vices wi | unce the quali Assembly Mat Il remain in cu | erial for the s | electe bly fac | d device ility: | es liste | |
| | Cu | rrent Si | te | | | Add | litional | al Site | |
| Current F | ab Site | Proc | cess | Wafer Diameter | Additional Fab Site | | Proces | S | Wafer Diameter |
| TSMC-WF2 | 2 (Fab 2) | TSMC/0 | | | RFAB | | LBC9 | | 300 mm |
| Assembly Materi | | Cur | rent | Pr | oposed | | | | |
| | | nil Cu | | | | | | | |
| Qual details | are provid | ded in th | e Qual [| Data Section. | | | | | |
| Reason for | | | | | | | | | |
| Continuity o | of Supply | | | | | | | | |
| | | | | | | | | | |
| Anticipate | d impact o | on Form | , Fit, F i | unction, Qua | lity or Relia | bility | (positi | ve / n | egative): |
| None | - | | | | lity or Relia | bility | (positi | ve / n | egative): |
| None Anticipate | d impact (| on Mate | rial De | claration | - | | | | |
| None Anticipate | - | on Mate | rial De Mate proc relea obta | claration erial Declarati luction data a ase. Upon pro ined at the si | ons or Produc nd will be ava oduction relea te link below | ct Con ailable ase the | tent rep followir e revise | orts ar ng the d repo | e driven from production rts can be |
| None Anticipate No In Mater | d impact of hpact to th rial Declara | on Mate e | rial De Mate proc relea obta <u>http</u> | claration erial Declarati luction data a ase. Upon pro ined at the si ://www.ti.cor | ons or Produc nd will be ava oduction relea te link below n/quality/doc | ct Con ailable ase the s/mat | tent rep followir e revise | orts ar ng the d repo | e driven from production rts can be |
| None Anticipate No In Mater | d impact of hpact to th rial Declara | on Mate e | rial De Mate proc relea obta <u>http</u> | claration erial Declarati luction data a ase. Upon pro ined at the si | ons or Produc nd will be ava oduction relea te link below n/quality/doc | ct Con ailable ase the s/mat | tent rep followir e revise | orts ar ng the d repo | e driven from production rts can be |
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| None Anticipate No In Mater Changes to Current: | d impact of hpact to th rial Declara | on Mate e ntion identifi | rial De Mate proc relea obta <u>http</u> | claration erial Declarati luction data a ase. Upon pro- ined at the si ://www.ti.cor resulting fro | ons or Produc nd will be ava oduction relea te link below n/quality/doc m this PCN: Chip Site 0 | ct Con ailable ase the s/mate | tent rep followir e revise erialcon | orts ar ng the d report tentsea | e driven from production rts can be |
| None Anticipate No In No In Mater Changes to Current: Current | d impact of hpact to the rial Declara | on Mate e ntion identifi | rial De Mate proc relea obta <u>http</u> cation | claration erial Declarati luction data a ase. Upon pro- ined at the si ://www.ti.cor resulting fro rigin Code L) | ons or Produc nd will be ava oduction relea te link below n/quality/doc: m this PCN: Chip Site 0 | ct Con ailable ase the s/mat | tent rep followir e revise erialcon | orts ar ng the d report tentsea | re driven from production rts can be arch.tsp |
| None Anticipate No In Mater Changes to Current: Current | d impact of hpact to the rial Declaration oproduct Chip Site 2 (Fab 2) | on Mate | rial De Mate proc relea obta <u>http</u> cation o Site O (20 TS | claration erial Declarati luction data a ase. Upon pro- ined at the si ://www.ti.cor resulting fro rigin Code L) | ons or Produc nd will be ava oduction relea te link below n/quality/doc m this PCN: Chip Site o (1 | ct Con ailable ase the s/mate S/mate Counte 21L) FWN | tent rep followir e revise erialcon | orts ar ng the d report tentsea | re driven from production rts can be arch.tsp Chip Site City |
| None Anticipate No In No In Mater Changes to Current: Current TSMC-WF New Fab S | d impact of hpact to the rial Declaration oproduct Chip Site 2 (Fab 2) | on Mate | rial De Mate proc relea obta <u>http</u> cation o Site O (20 TS | claration erial Declarati luction data a ase. Upon pro- ined at the si ://www.ti.cor resulting fro rigin Code L) 2 | ons or Produc nd will be ava oduction relea te link below n/quality/doc m this PCN: Chip Site (1 Chip Site (| ct Con ailable ase the s/mate S/mate Counte 21L) FWN | tent rep followir e revise erialcon | orts ar ng the d report tentsea | re driven from production rts can be arch.tsp Chip Site City |

| Die Rev: | | | | |
|------------------|--|---------------|--|-------------|
| Current | New | | | |
| Die Rev [2P] | Die Rev [2 | 2P] | | |
| В | Α | | | |
| | G4 G4 (EAR SEAL DT O3/29/04)T0:1750 | t actual prod | (1P) SN74LS07 (a) 2000 (31T) LOT: 39 | (D) 0336 |
| Product Affected | | DCKD | | |
| TMP75AID | TMP75AI | DGKR | TMP75AIDGKT | TMP75AIDR |
| TMP75AIDG4 | TMP75AI | | TMP75AIDGKTG4 | TMP75AIDRG4 |

Qualification Report

Approve Date 23-Jul-2020

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

| Туре | Test Name / Condition | Duration | Qual Device: <u>TMP75AIDGKR</u> | QBS Product Reference: <u>TMP1075DGKT</u> |
|-------------|-------------------------------|--------------------------|------------------------------------|--|
| ELFR | Early Life Failure Rate, 125C | 48 Hours | - | 3/2400/0 |
| HTOL | Life Test, 150C | 300 Hours | - | 3/231/0 |
| HTSL | High Temp Storage Bake 170C | 420 Hours | - | 3/231/0 |
| HAST | Biased HAST, 130C/85%RH | 96 Hours | - | 3/231/0 |
| UHAST | Unbiased HAST 130C/85%RH | 96 Hours | - | 3/244/0 |
| TC | Temperature Cycle, -65/150C | 500 Cycles | - | 3/231/0 |
| Power Cycle | Power on/off | 10000 Cycles | - | 3/231/0 |
| HBM | ESD - HBM | 4000 V | - | 1/3/0 |
| CDM | ESD - CDM | 1500 V | - | 1/3/0 |
| LU | Latch-up | (per JESD78) | - | 1/6/0 |
| ED | Electrical Characterization | Per Datasheet Parameters | - | 3/90/0 |
| WBP | Bond Pull | Wires | - | 3/240/0 |
| WBS | Bond Shear | Wires | - | 3/240/0 |

- QBS: Qual By Similarity

- Qual Device TMP75AIDGKR is qualified at LEVEL2-260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: <u>http://www.ti.com/</u>

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

Qualification Report

Approve Date 01-Sep-2020

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

| Туре | Test Name / Condition | Duration | Qual Device: <u>TMP75AIDR</u> | Qual Device: <u>TMP1075D</u> | QBS Product Reference: <u>TMP1075DGKT</u> |
|----------------|-------------------------------|-----------------------------|----------------------------------|---------------------------------|--|
| ELFR | Early Life Failure Rate, 125C | 48 Hours | - | - | 3/2400/0 |
| HTOL | Life Test, 150C | 300 Hours | - | - | 3/231/0 |
| HTSL | High Temp Storage Bake 170C | 420 Hours | - | 3/231/0 | - |
| HAST | Biased HAST, 130C/85%RH | 96 Hours | - | 3/231/0 | - |
| UHAST | Unbiased HAST 130C/85%RH | 96 Hours | - | 3/231/0 | - |
| TC | Temperature Cycle, -65/150C | 500 Cycles | - | 3/231/0 | - |
| Power Cycle | Power on/off | 10000 Cycles | - | - | 3/231/0 |
| HBM | ESD - HBM | 4000 V | - | - | 1/3/0 |
| CDM | ESD - CDM | 1500 V | - | 1/3/0 | - |
| LU | Latch-up | (per JESD78) | - | - | 1/6/0 |
| ED | Electrical Characterization | Per Datasheet Parameters | - | - | 3/90/0 |
| WBP | Bond Pull | Wires | - | 3/90/0 | - |
| WBS | Bond Shear | Wires | - | 3/90/0 | - |

- QBS: Qual By Similarity

- Qual Device TMP75D is qualified at LEVEL 1-260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

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|--------------|--------------------------------|
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| Asia Pacific | PCNAsiaContact@list.ti.com |
| WW PCN Team | PCN_ww_admin_team@list.ti.com |

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